



SMP30-xxx Series

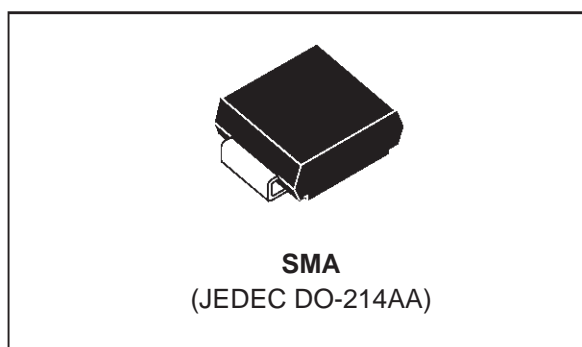
TRISIL™

FEATURES

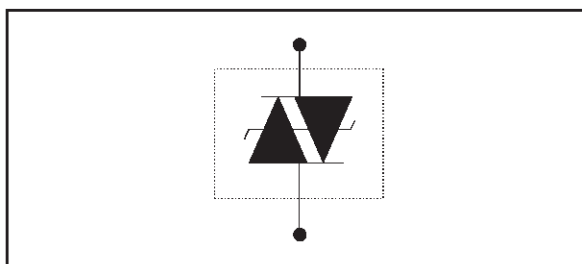
- BIDIRECTIONAL CROWBAR PROTECTION.
- VOLTAGE RANGE: FROM 62 V TO 270 V.
- HOLDING CURRENT :
 $I_H = 150 \text{ mA min.}$
- REPETITIVE PEAK PULSE CURRENT :
 $I_{PP} = 30 \text{ A, } 10/1000 \mu\text{s.}$
- JEDEC REGISTERED PACKAGE OUTLINE

DESCRIPTION

The SMP30-xxx series has been designed to protect telecommunication equipments against lightning surges and overvoltages induced by AC power lines.



SCHEMATIC DIAGRAM



COMPLIES WITH THE FOLLOWING STANDARDS:	Peak Surge Voltage (V)	Voltage Waveform (μs)	Current Waveform (μs)	Admissible I_{pp} (A)	Necessary Resistor (Ω)
(CCITT) ITU-K20	1000	10/700	5/310	25	-
(CCITT) ITU-K17	1500	10/700	5/310	38	-
VDE0433	2000	10/700	5/310	40	10
VDE0878	2000	1.2/50	1/20	50	-
IEC-1000-4-5	level 2 level 3	10/700 1.2/50	5/310 8/20	25 50	- -
FCC Part 68, lightning surge type A	1500 800	10/160 10/560	10/160 10/560	65 50	15.5 8.0
FCC Part 68, lightning surge type B	1000	9/720	5/320	25	-
BELLCORE TR-NWT-001089 First level	2500 1000	2/10 10/1000	2/10 10/1000	125 30	15.0 23.3
BELLCORE TR-NWT-001089 Second level	5000	2/10	2/10	125	15.0
BELLCORE TR-NWT-001089 Intra building lightning	1500	2/10	2/10	100	-
CNET I31-24	1000	0.5/700	0.8/310	25	-

SMP30-xxx Series

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25^{\circ}\text{C}$)

Symbol	Parameter		Value	Unit
P	Power dissipation on infinite heatsink	$T_{amb} = 50^{\circ}\text{C}$	3	W
I_{PP}	Peak pulse current	10/1000 μs 8/20 μs	30 60	A
I_{TSM}	Non repetitive surge peak on-state current	$t_p = 20 \text{ ms}$	15	A
I^2t	I^2t value for fusing	$t_p = 20 \text{ ms}$	1	A^2s
dV/dt	Critical rate of rise of off-state voltage	V_{RM}	5	$\text{kV}/\mu\text{s}$
T_{stg} T_j	Storage temperature range Maximum junction temperature		- 55 to + 150 150	$^{\circ}\text{C}$ $^{\circ}\text{C}$
T_L	Maximum lead temperature for soldering during 10s at 5mm for case		260	$^{\circ}\text{C}$

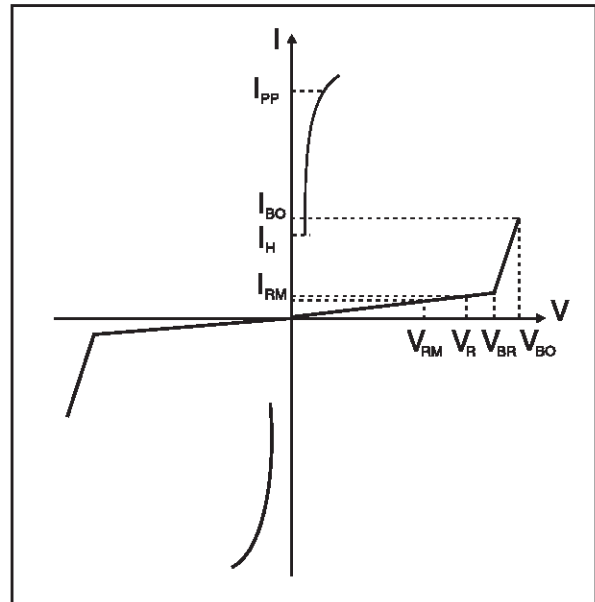
THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-l)}$	Junction to leads	30	$^{\circ}\text{C}/\text{W}$
$R_{th(j-a)}$	Junction to ambient on printed circuit with standard footprint dimension	120	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS

($T_{amb} = 25^{\circ}\text{C}$)

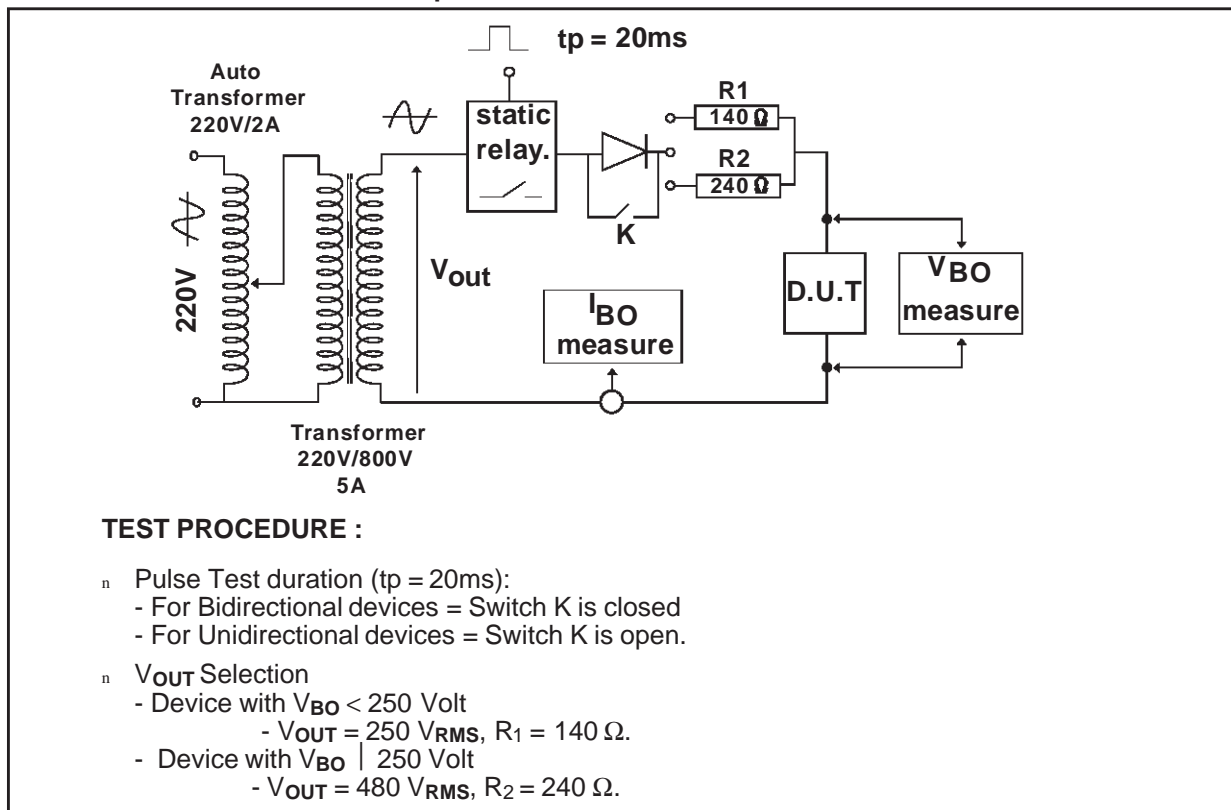
Symbol	Parameter
V_{RM}	Stand-off voltage
I_{RM}	Leakage current at stand-off voltage
V_R	Continuous Reverse voltage
V_{BR}	Breakdown voltage
V_{BO}	Breakover voltage
I_H	Holding current
I_{BO}	Breakover current
I_{PP}	Peak pulse current
C	Capacitance



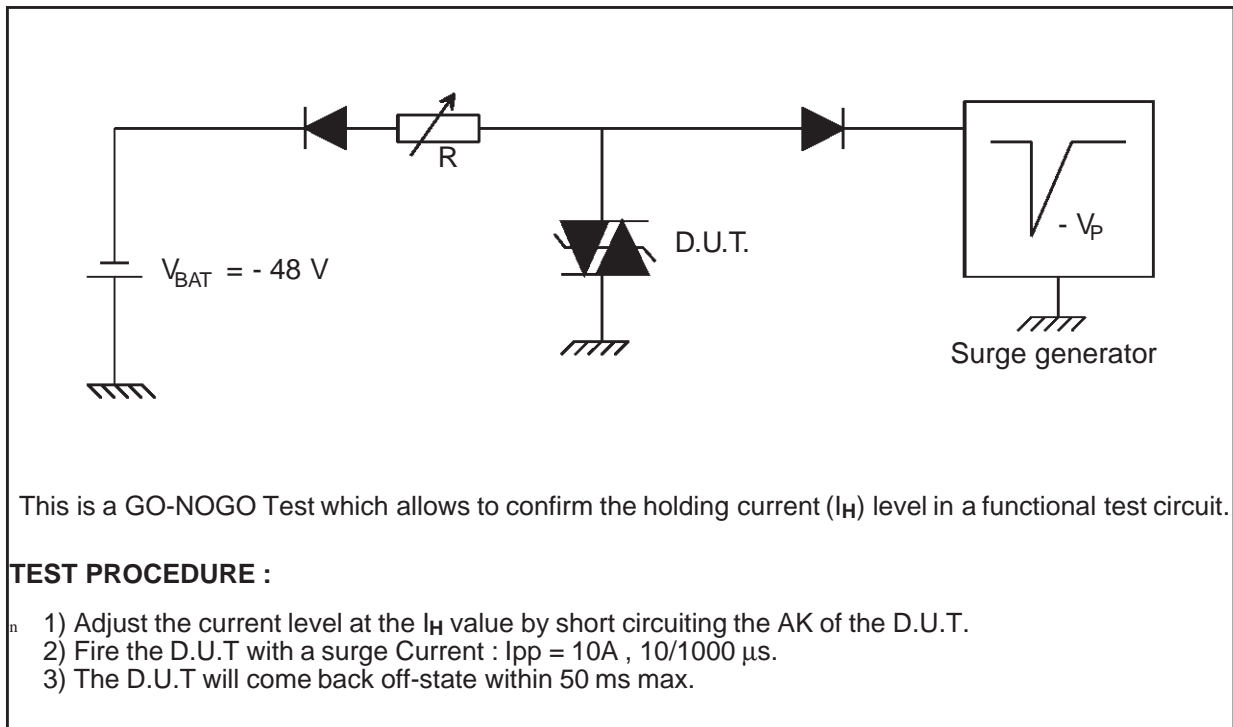
Type	Marking	I_{RM} @ V_{RM}		I_R @ V_R		V_{BO} @ I_{BO}		I_H min note 3 mA	C	
		max		max note 1		max note 2			typ note 4	typ note 5
		μA	V	μA	V	V	mA			
SMP30-62	QAA	2	56	50	62	82	800	150	50	20
SMP30-68	QAB	2	61	50	68	90	800	150	50	20
SMP30-100	QAC	2	90	50	100	133	800	150	40	16
SMP30-120	QAD	2	108	50	120	160	800	150	40	16
SMP30-130	QAE	2	117	50	130	173	800	150	35	14
SMP30-180	QAF	2	162	50	180	240	800	150	35	14
SMP30-200	QAG	2	180	50	200	267	800	150	30	12
SMP30-220	QAH	2	198	50	220	293	800	150	30	12
SMP30-240	QAI	2	216	50	240	320	800	150	30	12
SMP30-270	QAJ	2	243	50	270	360	800	150	30	12

- Note 1: I_R measured at V_R guarantee $V_{BRmin} \mid V_R$
- Note 2: Measured at 50 Hz (1 cycle) - See test circuit 1.
- Note 3: See test circuit 2.
- Note 4: $V_R = 1V, F = 1MHz$.
- Note 5: $V_R = 50V, F = 1MHz$

TEST CIRCUIT 1 FOR I_{BO} and V_{BO} parameters :



TEST CIRCUIT 2 for I_H parameter.



This is a GO-NOGO Test which allows to confirm the holding current (I_H) level in a functional test circuit.

TEST PROCEDURE :

- 1) Adjust the current level at the I_H value by short circuiting the AK of the D.U.T.
- 2) Fire the D.U.T with a surge Current : $I_{pp} = 10\text{ A}$, $10/1000\ \mu\text{s}$.
- 3) The D.U.T will come back off-state within 50 ms max.

Fig. 1: Non repetitive surge peak on-state current versus overload duration (T_j initial=25°C).

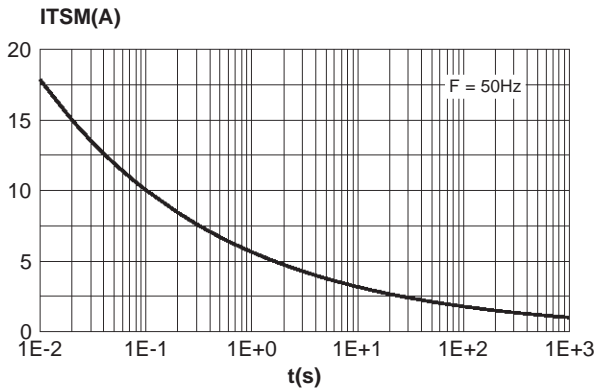


Fig. 2: Relative variation of holding current versus junction temperature.

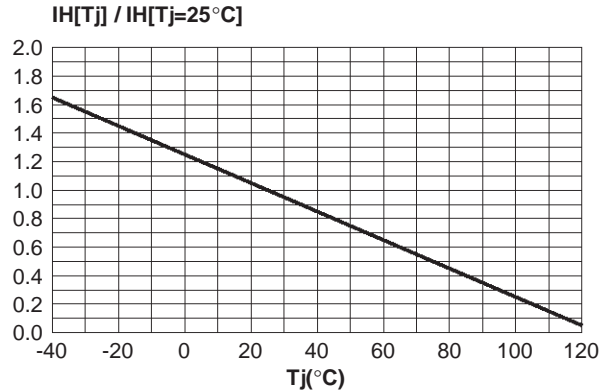


Fig. 3: Relative variation of junction capacitance versus reverse applied voltage (typical values)

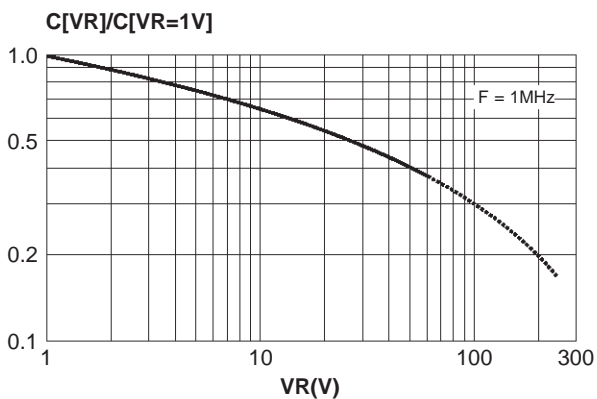


Fig. 4: On-state voltage versus on-state current (typical values).

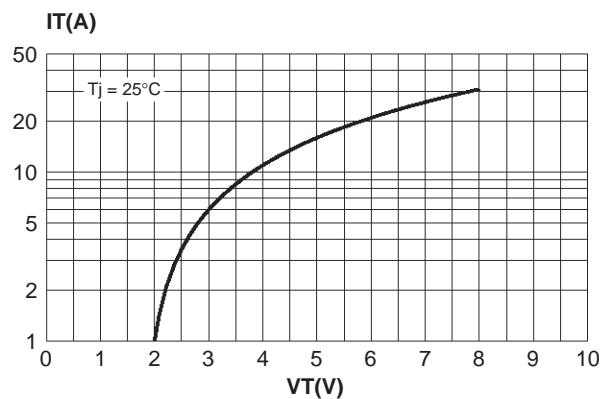


Fig. 5: Variation of thermal impedance junction to ambient versus pulse duration.

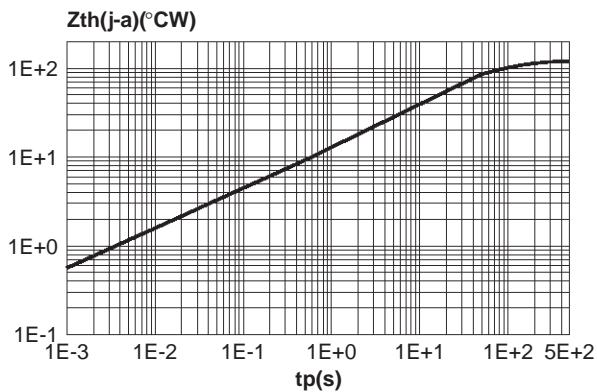
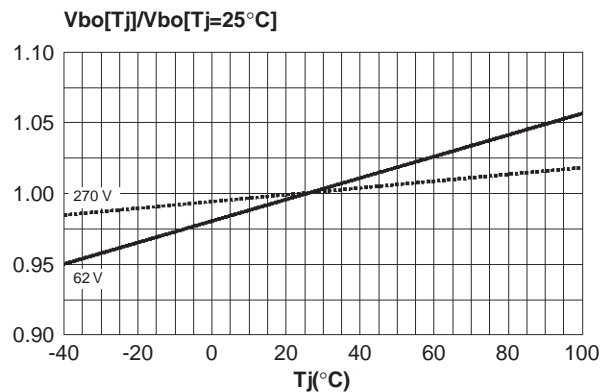
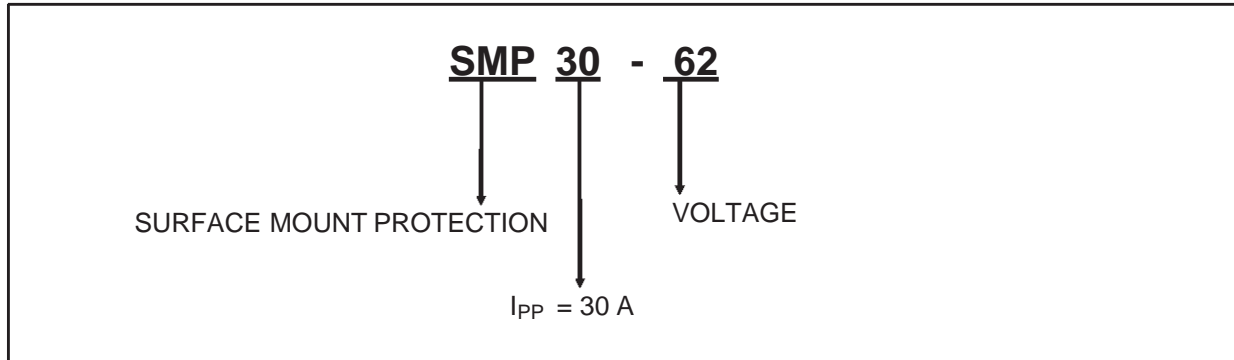


Fig. 6: Relative variation of V_{BO} voltage versus junction temperature.



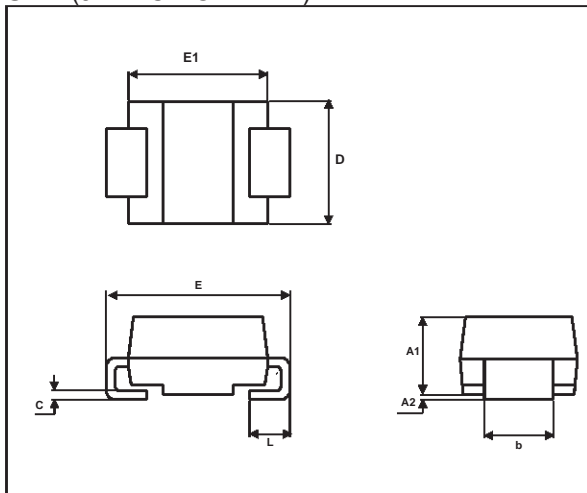
SMP30-xxx Series

ORDER CODE



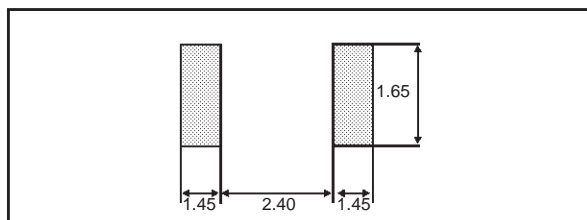
MARKING : Logo, Date Code, Part Number.

PACKAGE MECHANICAL DATA
SMA (JEDEC DO-214AA)



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A1	1.90	2.70	0.075	0.106
A2	0.05	0.20	0.002	0.008
b	1.25	1.65	0.049	0.065
c	0.15	0.41	0.006	0.016
E	4.80	5.60	0.189	0.220
E1	3.95	4.60	0.156	0.181
D	2.25	2.95	0.089	0.116
L	0.75	1.60	0.030	0.063

FOOT PRINT (in millimeters)



Weight: 0.06 g

Packaging : Tape and reel.

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